

TL07xx Low-Noise JFET-Input Operational Amplifiers

1 Features

- Low Power Consumption
- Wide Common-Mode and Differential Voltage Ranges
- Low Input Bias and Offset Currents
- Output Short-Circuit Protection
- Low Total Harmonic Distortion: 0.003% (Typical)
- Low Noise
 $V_n = 18 \text{ nV}/\sqrt{\text{Hz}}$ (Typical) at $f = 1 \text{ kHz}$
- High-Input Impedance: JFET Input Stage
- Internal Frequency Compensation
- Latch-Up-Free Operation
- High Slew Rate: $13 \text{ V}/\mu\text{s}$ (Typical)
- Common-Mode Input Voltage Range
Includes V_{CC+}

2 Applications

- Motor Integrated Systems: UPS
- Drives and Control Solutions: AC Inverter and VF Drives
- Renewables: Solar Inverters
- Pro Audio Mixers
- DLP Front Projection System
- Oscilloscopes

3 Description

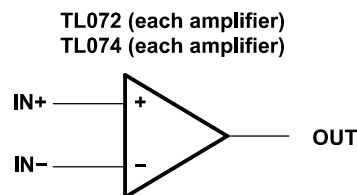
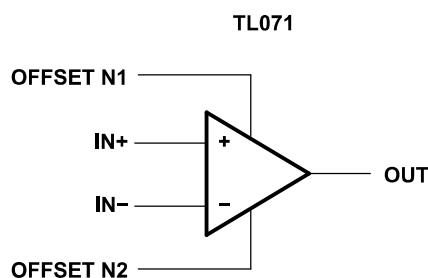
The TL07xx JFET-input operational amplifiers incorporate well-matched, high-voltage JFET and bipolar transistors in a monolithic integrated circuit. The devices feature high slew rates, low-input bias and offset currents, and low offset-voltage temperature coefficient. The low harmonic distortion and low noise make the TL07x series ideally suited for high-fidelity and audio pre-amplifier applications. The TL071 device has offset pins to support external input offset correction.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TL07xxD	SOIC (14)	8.65 mm × 3.91 mm
	SOIC (8)	4.90 mm × 3.90 mm
TL07xxJG	CDIP (8)	9.59 mm × 6.67 mm
TL074xJ	CDIP (14)	19.56 mm × 6.92 mm
TL07xxP	PDIP (8)	9.59 mm × 6.35 mm
TL07xxPS	SO (8)	6.20 mm × 5.30 mm
TL074xN	PDIP (14)	19.3 mm × 6.35 mm
TL074xNS	SO (14)	10.30 mm × 5.30 mm
TL07xxPW	TSSOP (8)	4.40 mm × 3.00 mm
TL074xPW	TSSOP (14)	5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Symbols



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision M (February 2014) to Revision N	Page
• Updated data sheet text to latest documentation and translation standards	1
• Added TL072M and TL074M devices to data sheet	1
• Rewrote text in <i>Description</i> section	1
• Changed TL07x 8-pin PDIP package to 8-pin CDIP package in <i>Device Information</i> table	1
• Deleted 20-pin LCCC package from <i>Device Information</i> table	1
• Added 2017 copyright statement to front page schematic	1
• Deleted TL071x FK (LCCC) pinout drawing and pinout table in <i>Pin Configurations and Functions</i> section	4
• Updated pinout diagrams and pinout tables in <i>Pin Configurations and Functions</i> section	5
• Deleted differential input voltage parameter from <i>Absolute Maximum Ratings</i> table	10
• Deleted table notes from <i>Absolute Maximum Ratings</i> table	10
• Added new table note to <i>Absolute Maximum Ratings</i> table	10
• Changed minimum supply voltage value from –18 V to –0.3 V in <i>Absolute Maximum Ratings</i> table	10
• Changed maximum supply voltage from 18 V to 36 V in <i>Absolute Maximum Ratings</i> table	10
• Changed minimum input voltage value from –15 V to $V_{CC-} - 0.3$ V in <i>Absolute Maximum Ratings</i> table	10
• Changed maximum input voltage from 15 V to $V_{CC+} + 36$ V in <i>Absolute Maximum Ratings</i> table	10
• Added input clamp current parameter to <i>Absolute Maximum Ratings</i> table	10
• Changed common-mode voltage maximum value from $V_{CC+} - 4$ V to V_{CC+} in the <i>Recommended Operating Conditions</i> table	10

Revision History (continued)

• Changed devices in <i>Recommended Operating Conditions</i> table from TL07xA and TL07xB to TL07xAC and TL07xBC	10
• Added TL07xI operating free-air temperature minimum value of –40°C to <i>Recommended Operating Conditions</i> table ...	10
• Added U (CFP) package thermal values to <i>Thermal Information: TL072x (cont.)</i> table	11
• Added W (CFP) package thermal values to <i>Thermal Information: TL074x (cont.)</i> table	12
• Added Figure 20 to Table 1	20
• Added Figure 20 to <i>Typical Characteristics</i> section	24
• Added second <i>Typical Application</i> section application curves	29
• Reformatted document references in <i>Layout Guidelines</i> section	32
• Updated formatting of document reference in <i>Related Documentation</i> section	34

Changes from Revision L (February 2014) to Revision M
Page

• Added <i>Device Information</i> table, <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes, Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section	1
• Moved <i>Typical Characteristics</i> into <i>Specifications</i> section.	20

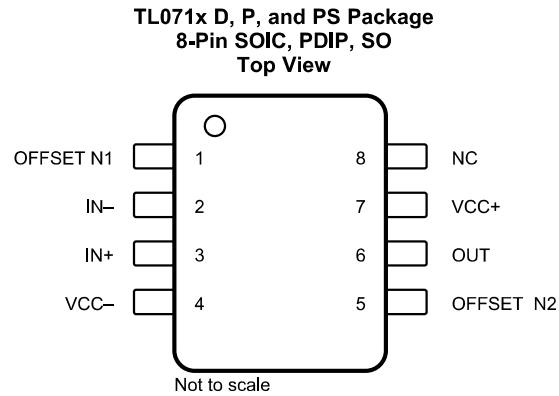
Changes from Revision K (January 2014) to Revision L
Page

• Moved T_{stg} to <i>Handling Ratings</i> table	10
• Added <i>Device and Documentation Support</i> section	34
• Added <i>Mechanical, Packaging, and Orderable Information</i> section.....	34

Changes from Revision J (March 2005) to Revision K
Page

• Updated document to new TI datasheet format - no specification changes.	1
• Added ESD warning	34

5 Pin Configuration and Functions

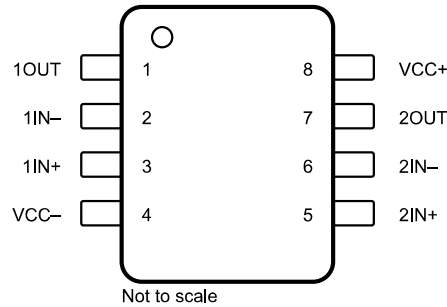


NC- no internal connection

Pin Functions: TL071x

PIN		I/O	DESCRIPTION
NAME	NO.		
IN-	2	I	Inverting input
IN+	3	I	Noninverting input
NC	8	—	Do not connect
OFFSET N1	1	—	Input offset adjustment
OFFSET N2	5	—	Input offset adjustment
OUT	6	O	Output
VCC-	4	—	Power supply
VCC+	7	—	Power supply

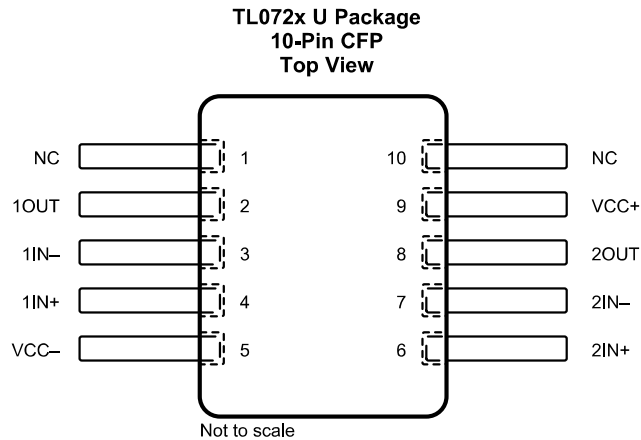
**TL072x D, JG, P, PS and PW Package
8-Pin SOIC, CDIP, PDIP, SO
Top View**



Not to scale

Pin Functions: TL072x

PIN		I/O	DESCRIPTION
NAME	NO.		
1IN-	2	I	Inverting input
1IN+	3	I	Noninverting input
1OUT	1	O	Output
2IN-	6	I	Inverting input
2IN+	5	I	Noninverting input
2OUT	7	O	Output
VCC-	4	—	Power supply
VCC+	8	—	Power supply

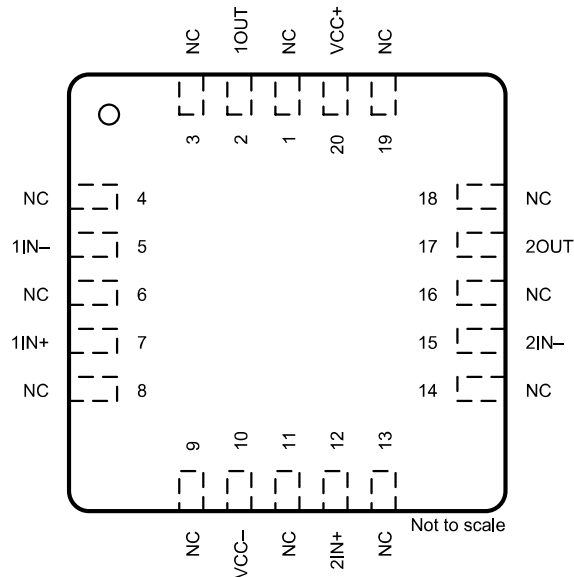


NC- no internal connection

Pin Functions: TL072x

PIN		I/O	DESCRIPTION
NAME	NO.		
1IN-	3	I	Inverting input
1IN+	4	I	Noninverting input
1OUT	2	O	Output
2IN-	7	I	Inverting input
2IN+	6	I	Noninverting input
2OUT	8	O	Output
NC	1, 10	—	Do not connect
VCC-	5	—	Power supply
VCC+	9	—	Power supply

**TL072 FK Package
20-Pin LCCC
Top View**

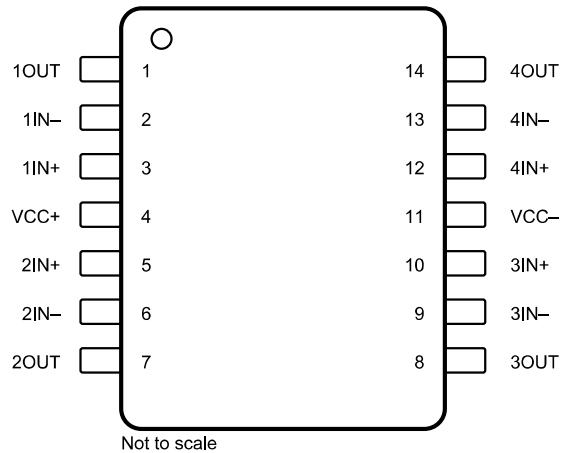


NC- no internal connection

Pin Functions: TL072x

PIN		I/O	DESCRIPTION
NAME	NO.		
1IN-	5	I	Inverting input
1IN+	7	I	Noninverting input
1OUT	2	O	Output
2IN-	15	I	Inverting input
2IN+	12	I	Noninverting input
2OUT	17	O	Output
NC	1, 3, 4, 6, 8, 9, 11, 13, 14, 16, 18, 19	—	Do not connect
VCC-	10	—	Power supply
VCC+	20	—	Power supply

TL074 D, N, NS, PW, J, and W Packages
 14-Pin SOIC, PDIP, SO, TSSOP, CDIP and CFP
 Top View

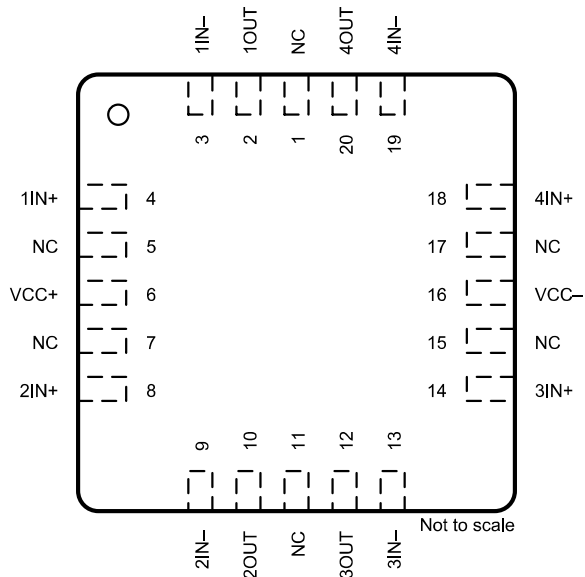


Not to scale

Pin Functions: TL074x

PIN		I/O	DESCRIPTION
NAME	NO.		
1IN-	2	I	Inverting input
1IN+	3	I	Noninverting input
1OUT	1	O	Output
2IN-	6	I	Inverting input
2IN+	5	I	Noninverting input
2OUT	7	O	Output
3IN-	9	I	Inverting input
3IN+	10	I	Noninverting input
3OUT	8	O	Output
4IN-	13	I	Inverting input
4IN+	12	I	Noninverting input
4OUT	14	O	Output
V _{CC-}	11	—	Power supply
V _{CC+}	4	—	Power supply

**TL074 FK Package
20-Pin LCCC
Top View**



NC- no internal connection

Pin Functions: TL074x

PIN		I/O	DESCRIPTION
NAME	NO.		
1IN-	3	I	Inverting input
1IN+	4	I	Noninverting input
1OUT	2	O	Output
2IN-	9	I	Inverting input
2IN+	8	I	Noninverting input
2OUT	10	O	Output
3IN-	13	I	Inverting input
3IN+	14	I	Noninverting input
3OUT	12	O	Output
4IN-	19	I	Inverting input
4IN+	18	I	Noninverting input
4OUT	20	O	Output
NC	1, 5, 7, 11, 15, 17	—	Do not connect
VCC-	16	—	Power supply
VCC+	6	—	Power supply

6 Specifications

6.1 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
$V_{CC+} - V_{CC-}$	Supply voltage	-0.3	36	V
V_I	Input voltage ⁽²⁾	$V_{CC-} - 0.3$	$V_{CC-} + 36$	V
I_{IK}	Input clamp current		-50	mA
	Duration of output short circuit ⁽³⁾	Unlimited		
T_J	Operating virtual junction temperature		150	°C
	Case temperature for 60 seconds - FK package		260	°C
	Lead temperature 1.8 mm (1/16 inch) from case for 10 seconds		300	°C
T_{stg}	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Differential voltage only limited by input voltage.
- (3) The output may be shorted to ground or to either supply. Temperature and supply voltages must be limited to ensure that the dissipation rating is not exceeded.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge		
	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT	
V_{CC+}	Supply voltage ⁽¹⁾	5	15	V	
V_{CC-}	Supply voltage ⁽¹⁾	-5	-15	V	
V_{CM}	Common-mode voltage	$V_{CC-} + 4$	V_{CC+}	V	
T_A	Operating free-air temperature	TL07xM	-55	125	°C
		TL08xQ	-40	125	
		TL07xI	-40	85	
		TL07xAC, TL07xBC, TL07xC	0	70	

- (1) V_{CC+} and V_{CC-} are not required to be of equal magnitude, provided that the total V_{CC} ($V_{CC+} - V_{CC-}$) is between 10 V and 30 V.

6.4 Thermal Information: TL071x

THERMAL METRIC ⁽¹⁾		TL071x			UNIT
		D (SOIC)	P (PDIP)	PS (SO)	
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97	85	95	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	—	—	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Thermal Information: TL072x

THERMAL METRIC ⁽¹⁾		TL072x				UNIT
		D (SOIC)	JG (CDIP)	P (PDIP)	PS (SO)	
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	97	—	85	95	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	—	15.05	—	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.6 Thermal Information: TL072x (cont.)

THERMAL METRIC ⁽¹⁾		TL072x			UNIT
		PW (TSSOP)	U (CFP)	FK (LCCC)	
		8 PINS	10 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	150	169.8	—	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	—	62.1	5.61	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	—	176.2	—	°C/W
ψ_{JT}	Junction-to-top characterization parameter	—	48.4	—	°C/W
ψ_{JB}	Junction-to-board characterization parameter	—	144.1	—	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	5.4	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.7 Thermal Information: TL074x

THERMAL METRIC ⁽¹⁾		TL074x			UNIT
		D (SOIC)	N (PDIP)	NS (SO)	
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86	80	76	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	—	—	—	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.8 Thermal Information: TL074x (cont).

THERMAL METRIC ⁽¹⁾	TL074x			UNIT
	J (CDIP)	PW (TSSOP)	W (CFP)	
	14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$ Junction-to-ambient thermal resistance	—	113	128.8	°C/W
$R_{\theta JC(top)}$ Junction-to-case (top) thermal resistance	14.5	—	56.1	°C/W
$R_{\theta JB}$ Junction-to-board thermal resistance	—	—	127.6	°C/W
ψ_{JT} Junction-to-top characterization parameter	—	—	29	°C/W
ψ_{JB} Junction-to-board characterization parameter	—	—	106.1	°C/W
$R_{\theta JC(bot)}$ Junction-to-case (bottom) thermal resistance	—	—	0.5	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.9 Thermal Information: TL074x (cont).

THERMAL METRIC ⁽¹⁾	TL074x		UNIT
	FK (LCCC)		
	20 PINS		
$R_{\theta JA}$ Junction-to-ambient thermal resistance	—		°C/W
$R_{\theta JC(top)}$ Junction-to-case (top) thermal resistance	5.61		°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.10 Electrical Characteristics: TL071C, TL072C, TL074C

 $V_{CC\pm} = \pm 15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽¹⁾ ⁽²⁾		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$		3	10	mV
			$T_A = \text{Full range}$			13	
α	Temperature coefficient of input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = \text{Full range}$		18		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$		5	100	pA
			$T_A = \text{Full range}$			10	nA
I_{IB}	Input bias current ⁽³⁾	$V_O = 0$	$T_A = 25^\circ\text{C}$		65	200	pA
			$T_A = \text{Full range}$			7	nA
V_{ICR}	Common-mode input voltage range	$T_A = 25^\circ\text{C}$		± 11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	± 12	± 13.5		V
		$R_L \geq 10\ \text{k}\Omega$	$T_A = \text{Full range}$	± 12			
		$R_L \geq 2\ \text{k}\Omega$		± 10			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ $R_L \geq 2\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	25	200		V/mV
			$T_A = \text{Full range}$	15			
B_1	Utility-gain bandwidth	$T_A = 25^\circ\text{C}$			3		MHz
r_i	Input resistance	$T_A = 25^\circ\text{C}$			10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR(\text{min})}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	70	100		dB
k_{SVR}	Supply voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	70	100		dB
I_{CC}	Supply current (each amplifier)	$V_O = 0$; no load	$T_A = 25^\circ\text{C}$		1.4	2.5	mA
V_{O1} / V_{O2}	Crosstalk attenuation	$A_{VD} = 100$	$T_A = 25^\circ\text{C}$		120		dB

(1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified.

(2) Full range is $T_A = 0^\circ\text{C}$ to 70°C .

(3) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in [Figure 1](#). Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

6.11 Electrical Characteristics: TL071AC, TL072AC, TL074AC

$V_{CC\pm} = \pm 15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽¹⁾ ⁽²⁾		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	3	6	7.5	mV
			$T_A = \text{Full range}$				
α	Temperature coefficient of input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = \text{Full range}$		18		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$	5	100	2	pA
			$T_A = \text{Full range}$				
I_{IB}	Input bias current ⁽³⁾	$V_O = 0$	$T_A = 25^\circ\text{C}$	65	200	7	pA
			$T_A = \text{Full range}$				
V_{ICR}	Common-mode input voltage range	$T_A = 25^\circ\text{C}$		± 11	-12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	± 12	± 13.5		V
		$R_L \geq 10\ \text{k}\Omega$	$T_A = \text{Full range}$	± 12			
		$R_L \geq 2\ \text{k}\Omega$		± 10			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ $R_L \geq 2\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	50	200		V/mV
			$T_A = \text{Full range}$	25			
B_1	Utility-gain bandwidth	$T_A = 25^\circ\text{C}$			3		MHz
r_i	Input resistance	$T_A = 25^\circ\text{C}$			10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR(\text{min})}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	75	100		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	100		dB
I_{CC}	Supply current (each amplifier)	$V_O = 0$; no load			1.4	2.5	mA
V_{O1} / V_{O2}	Crosstalk attenuation	$A_{VD} = 100$			120		dB

- (1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified.
- (2) Full range is $T_A = 0^\circ\text{C}$ to 70°C .
- (3) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in [Figure 1](#). Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

6.12 Electrical Characteristics: TL071BC, TL072BC, TL074BC

 $V_{CC\pm} = \pm 15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽¹⁾ ⁽²⁾		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$		2	3	mV
			$T_A = \text{Full range}$			5	
α	Temperature coefficient of input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = \text{Full range}$		18		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$		5	100	pA
			$T_A = \text{Full range}$				2
I_{IB}	Input bias current ⁽³⁾	$V_O = 0$	$T_A = 25^\circ\text{C}$		65	200	pA
			$T_A = \text{Full range}$				7
V_{ICR}	Common-mode input voltage range	$T_A = 25^\circ\text{C}$		± 11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	± 12	± 13.5		V
		$R_L \geq 10\ \text{k}\Omega$	$T_A = \text{Full range}$	± 12			
		$R_L \geq 2\ \text{k}\Omega$		± 10			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ $R_L \geq 2\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	50	200		V/mV
			$T_A = \text{Full range}$	25			
B_1	Utility-gain bandwidth	$T_A = 25^\circ\text{C}$			3		MHz
r_i	Input resistance	$T_A = 25^\circ\text{C}$			10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR(\text{min})}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	75	100		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	100		dB
I_{CC}	Supply current (each amplifier)	$V_O = 0$; no load		$T_A = 25^\circ\text{C}$	1.4	2.5	mA
V_{O1} / V_{O2}	Crosstalk attenuation	$A_{VD} = 100$		$T_A = 25^\circ\text{C}$	120		dB

- (1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified.
- (2) Full range is $T_A = 0^\circ\text{C}$ to 70°C .
- (3) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in [Figure 1](#). Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

6.13 Electrical Characteristics: TL071I, TL072I, TL074I

$V_{CC\pm} = \pm 15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽¹⁾ ⁽²⁾		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$		3	6	mV
			$T_A = \text{Full range}$			8	
α	Temperature coefficient of input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = \text{Full range}$		18		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$		5	100	pA
			$T_A = \text{Full range}$				2
I_{IB}	Input bias current ⁽³⁾	$V_O = 0$	$T_A = 25^\circ\text{C}$		65	200	pA
			$T_A = \text{Full range}$				7
V_{ICR}	Common-mode input voltage range	$T_A = 25^\circ\text{C}$		± 11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	± 12	± 13.5		V
		$R_L \geq 10\ \text{k}\Omega$	$T_A = \text{Full range}$	± 12			
		$R_L \geq 2\ \text{k}\Omega$		± 10			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ $R_L \geq 2\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	50	200		V/mV
			$T_A = \text{Full range}$	25			
B_1	Utility-gain bandwidth	$T_A = 25^\circ\text{C}$			3		MHz
r_i	Input resistance	$T_A = 25^\circ\text{C}$			10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR(\text{min})}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	75	100		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	100		dB
I_{CC}	Supply current (each amplifier)	$V_O = 0$; no load		$T_A = 25^\circ\text{C}$	1.4	2.5	mA
V_{O1} / V_{O2}	Crosstalk attenuation	$A_{VD} = 100$		$T_A = 25^\circ\text{C}$	120		dB

- (1) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified.
- (2) $T_A = -40^\circ\text{C}$ to 85°C .
- (3) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in [Figure 1](#). Pulse techniques must be used that maintain the junction temperature as close to the ambient temperature as possible.

6.14 Electrical Characteristics: TL071M, TL072M

 $V_{CC\pm} = \pm 15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽¹⁾ ⁽²⁾		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$		3	6	mV
			$T_A = \text{Full range}$			9	
α_{VIO}	Temperature coefficient of input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = \text{Full range}$		18		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$		5	100	pA
			$T_A = \text{Full range}$			20	nA
I_{IB}	Input bias current	$V_O = 0$	$T_A = 25^\circ\text{C}$		65	200	pA
			$T_A = \text{Full range}$			50	nA
V_{ICR}	Common-mode input voltage range	$T_A = 25^\circ\text{C}$		± 11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	± 12	± 13.5		V
		$R_L \geq 10\ \text{k}\Omega$	$T_A = \text{Full range}$	± 12			
		$R_L \geq 2\ \text{k}\Omega$		± 10			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ $R_L \geq 2\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	35	200		V/mV
			$T_A = \text{Full range}$	15			
B_1	Unity-gain bandwidth				3		MHz
r_i	Input resistance				10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR(\text{min})}$, $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	86		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	86		dB
I_{CC}	Supply current (each amplifier)	$V_O = 0$; no load	$T_A = 25^\circ\text{C}$		1.4	2.5	mA
V_{O1} / V_{O2}	Crosstalk attenuation	$A_{VD} = 100$	$T_A = 25^\circ\text{C}$		120		dB

- (1) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in [Figure 1](#). Pulse techniques that maintain the junction temperature as close to the ambient temperature as possible must be used.
- (2) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified. Full range is $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$.

6.15 Electrical Characteristics: TL074M

$V_{CC\pm} = \pm 15\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽¹⁾ ⁽²⁾		MIN	TYP	MAX	UNIT
V_{IO}	Input offset voltage	$V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$		3	9	mV
			$T_A = \text{Full range}$			15	
α_{VIO}	Temperature coefficient of input offset voltage	$V_O = 0, R_S = 50\ \Omega$	$T_A = \text{Full range}$		18		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input offset current	$V_O = 0$	$T_A = 25^\circ\text{C}$		5	100	pA
			$T_A = \text{Full range}$			20	nA
I_{IB}	Input bias current	$V_O = 0$	$T_A = 25^\circ\text{C}$		65	200	pA
			$T_A = \text{Full range}$			20	nA
V_{ICR}	Common-mode input voltage range	$T_A = 25^\circ\text{C}$		± 11	–12 to 15		V
V_{OM}	Maximum peak output voltage swing	$R_L = 10\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	± 12	± 13.5		V
		$R_L \geq 10\ \text{k}\Omega$	$T_A = \text{Full range}$	± 12			
		$R_L \geq 2\ \text{k}\Omega$		± 10			
A_{VD}	Large-signal differential voltage amplification	$V_O = \pm 10\ \text{V}$ $R_L \geq 2\ \text{k}\Omega$	$T_A = 25^\circ\text{C}$	35	200		V/mV
			$T_A = \text{Full range}$	15			
B_1	Unity-gain bandwidth				3		MHz
r_i	Input resistance				10^{12}		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR(\text{min})}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	86		dB
k_{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$)	$V_{CC} = \pm 9\ \text{V}$ to $\pm 15\ \text{V}$ $V_O = 0$ $R_S = 50\ \Omega$	$T_A = 25^\circ\text{C}$	80	86		dB
I_{CC}	Supply current (each amplifier)	$V_O = 0$; no load	$T_A = 25^\circ\text{C}$		1.4	2.5	mA
V_{O1} / V_{O2}	Crosstalk attenuation	$A_{VD} = 100$	$T_A = 25^\circ\text{C}$		120		dB

- (1) Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive, as shown in Figure 1. Pulse techniques that maintain the junction temperature as close to the ambient temperature as possible must be used.
- (2) All characteristics are measured under open-loop conditions with zero common-mode voltage, unless otherwise specified. Full range is $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$.

6.16 Switching Characteristics: TL07xM

 $V_{CC\pm} = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$V_I = 10\text{ V}$ $C_L = 100\text{ pF}$	$R_L = 2\text{ k}\Omega$ See Figure 21	5	13		$\text{V}/\mu\text{s}$
t_r	Rise-time overshoot factor	$V_I = 20\text{ V}$ $C_L = 100\text{ pF}$	$R_L = 2\text{ k}\Omega$ See Figure 21		0.1		μs
					20%		
V_n	Equivalent input noise voltage	$R_S = 20\ \Omega$	$f = 1\text{ kHz}$		18		$\text{nV}/\sqrt{\text{Hz}}$
			$f = 10\text{ Hz to } 10\text{ kHz}$		4		μV
I_n	Equivalent input noise current	$R_S = 20\ \Omega$	$f = 1\text{ kHz}$		0.01		$\text{pA}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion	$V_{\text{rms}} = 6\text{ V}$ $R_L \geq 2\text{ k}\Omega$ $f = 1\text{ kHz}$	$A_{\text{VD}} = 1$ $R_S \leq 1\text{ k}\Omega$		0.003%		

6.17 Switching Characteristics: TL07xC, TL07xAC, TL07xBC, TL07xI

 $V_{CC\pm} = \pm 15\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$V_I = 10\text{ V}$ $C_L = 100\text{ pF}$	$R_L = 2\text{ k}\Omega$ See Figure 21	8	13		$\text{V}/\mu\text{s}$
t_r	Rise-time overshoot factor	$V_I = 20\text{ V}$ $C_L = 100\text{ pF}$	$R_L = 2\text{ k}\Omega$ See Figure 21		0.1		μs
					20%		
V_n	Equivalent input noise voltage	$R_S = 20\ \Omega$	$f = 1\text{ kHz}$		18		$\text{nV}/\sqrt{\text{Hz}}$
			$f = 10\text{ Hz to } 10\text{ kHz}$		4		μV
I_n	Equivalent input noise current	$R_S = 20\ \Omega$	$f = 1\text{ kHz}$		0.01		$\text{pA}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion	$V_{\text{rms}} = 6\text{ V}$ $R_L \geq 2\text{ k}\Omega$ $f = 1\text{ kHz}$	$A_{\text{VD}} = 1$ $R_S \leq 1\text{ k}\Omega$		0.003%		

6.18 Typical Characteristics

Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

Table 1. Typical Characteristics: Table of Graphs

			FIGURE
I_{IB}	Input bias current	versus free-air temperature	Figure 1
V_{OM}	Maximum peak output voltage	versus frequency	Figure 2
			Figure 3
			Figure 4
		versus free-air temperature	Figure 5
		versus load resistance	Figure 6
	versus supply voltage	Figure 7	
A_{VD}	Large signal differential voltage amplification	versus free-air temperature	Figure 8
		versus load resistance	Figure 9
	Phase shift	versus frequency	Figure 9
	Normalized unity-gain bandwidth	versus free-air temperature	Figure 10
	Normalized phase shift	versus free-air temperature	Figure 10
CMRR	Common-mode rejection ratio	versus free-air temperature	Figure 11
	Input offset voltage change	versus common-mode voltage	Figure 20
I_{CC}	Supply current	versus free-air temperature	Figure 13
		versus supply voltage	Figure 12
P_D	Total power dissipation	versus free-air temperature	Figure 14
	Normalized slew rate	versus free-air temperature	Figure 15
V_n	Equivalent input noise voltage	versus frequency	Figure 16
THD	Total harmonic distortion	versus frequency	Figure 17
	Large-signal pulse response	versus time	Figure 18
V_O	Output voltage	versus elapsed time	Figure 19

6.18.1 Typical Characteristics

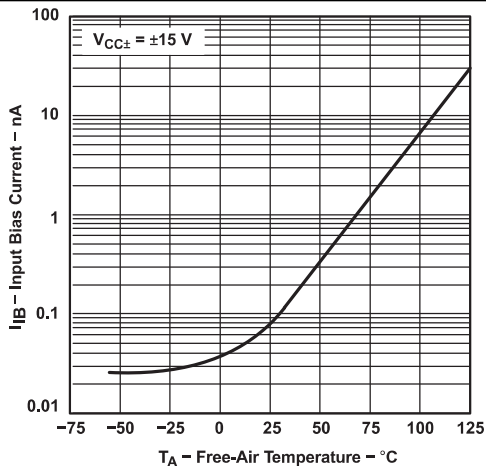


Figure 1. Input Bias Current vs Free-Air Temperature

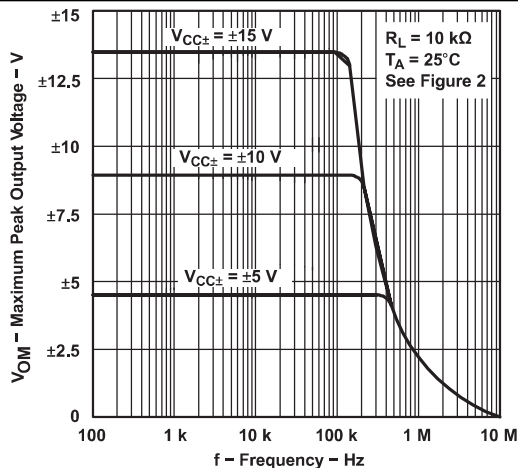


Figure 2. Maximum Peak Output Voltage vs Frequency

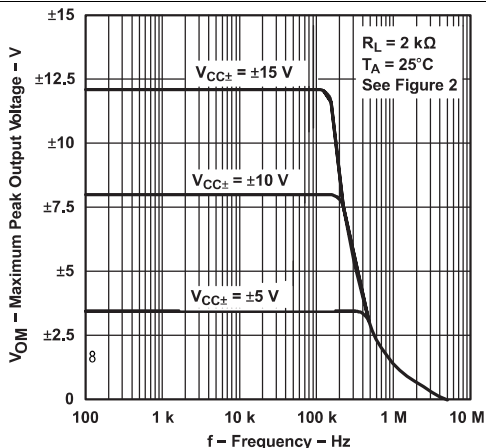


Figure 3. Maximum Peak Output Voltage vs Frequency

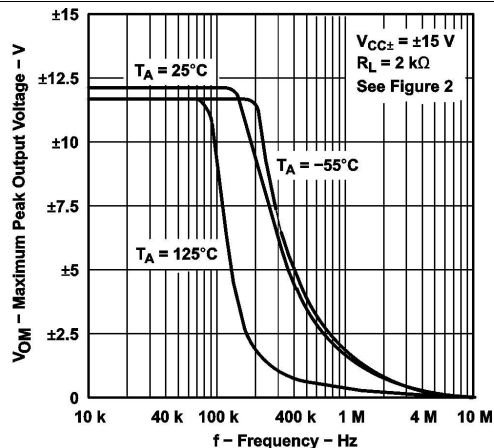


Figure 4. Maximum Peak Output Voltage vs Frequency

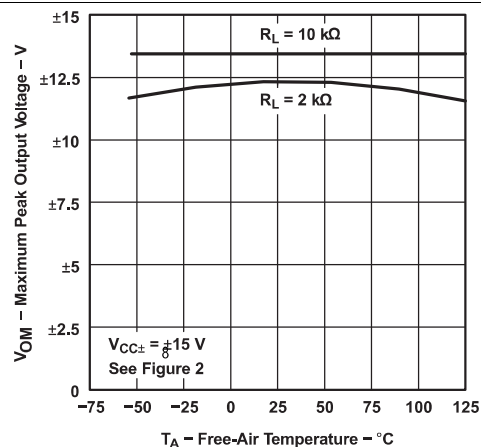


Figure 5. Maximum Peak Output Voltage vs Free-Air Temperature

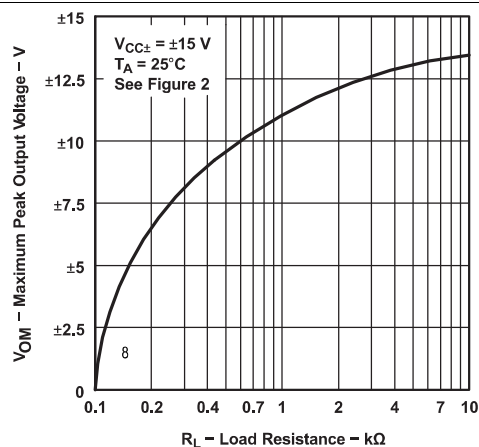
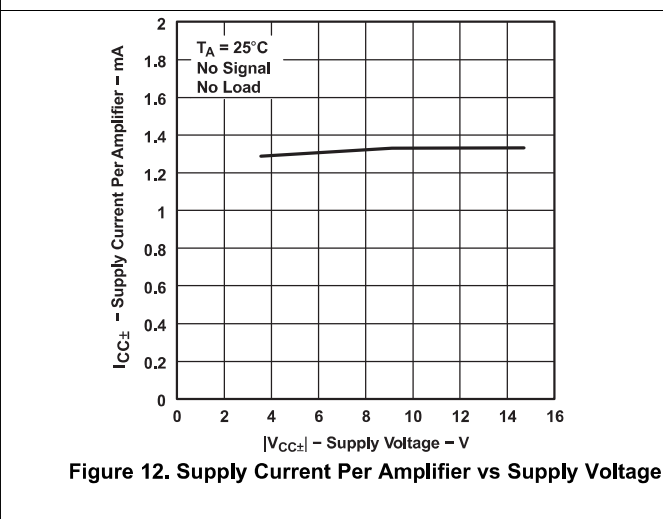
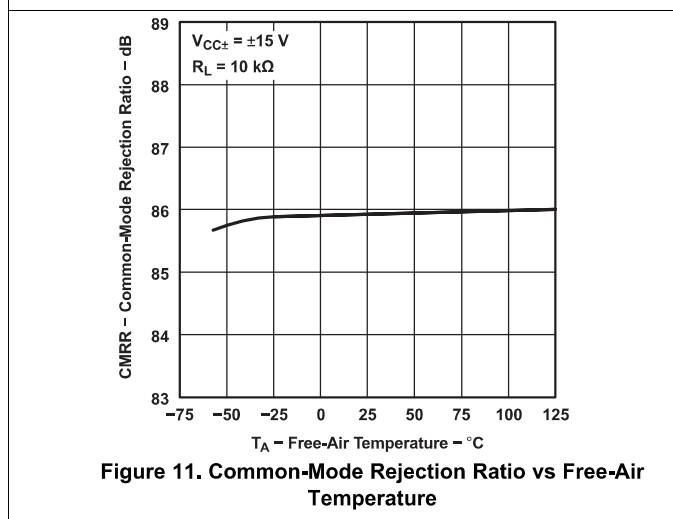
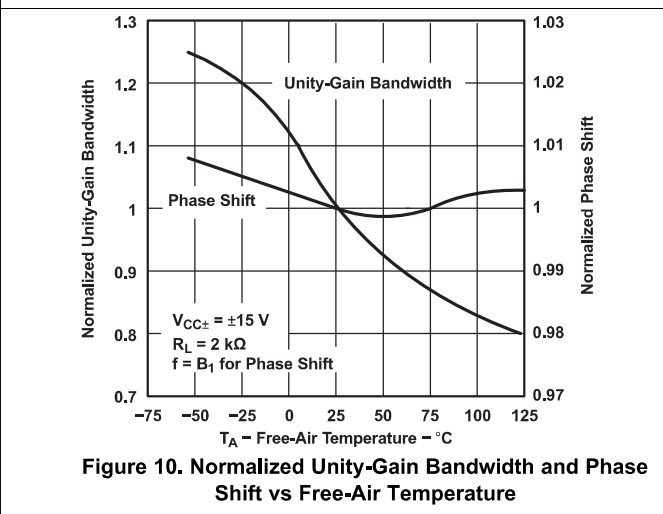
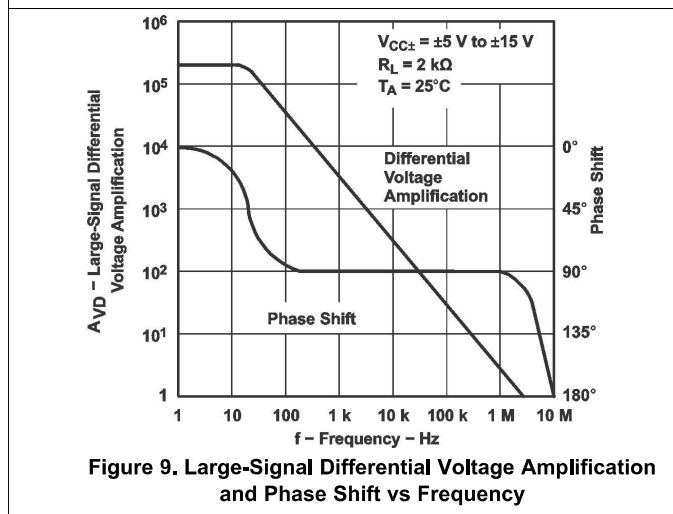
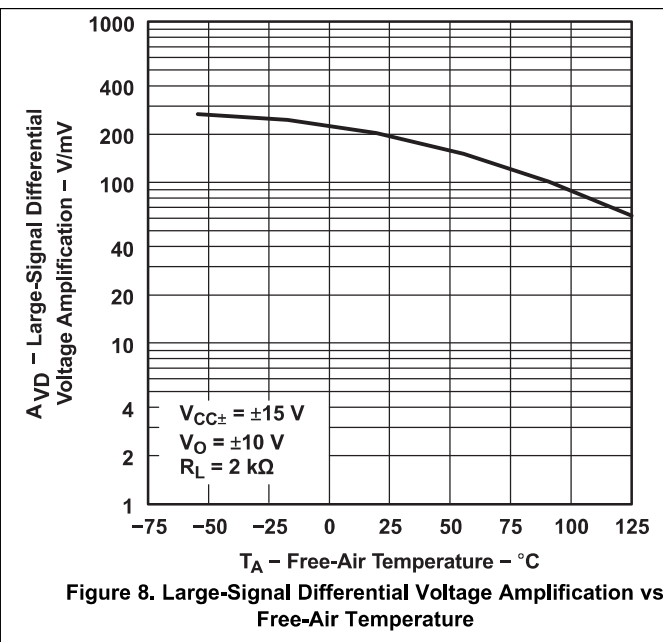
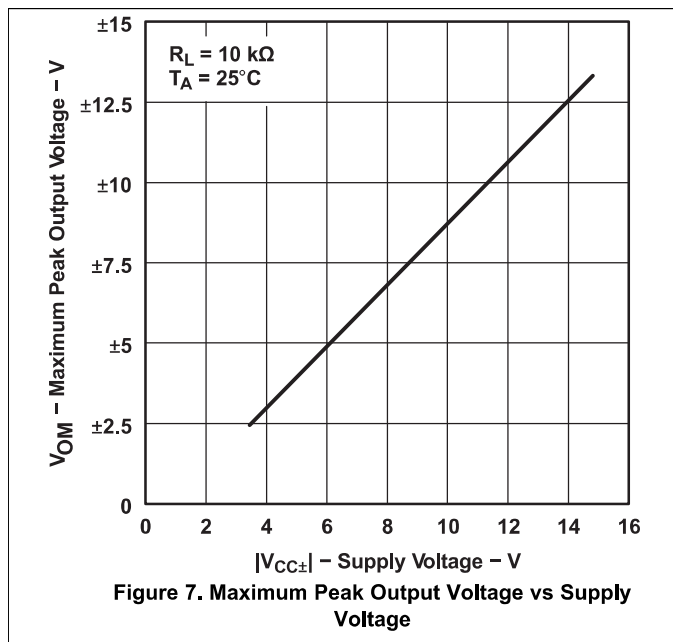


Figure 6. Maximum Peak Output Voltage vs Load Resistance

Typical Characteristics (continued)



Typical Characteristics (continued)

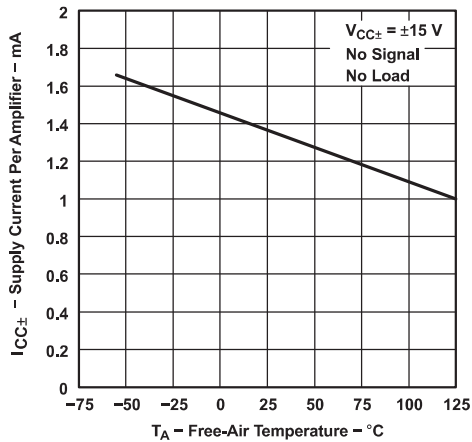


Figure 13. Supply Current Per Amplifier vs Free-Air Temperature

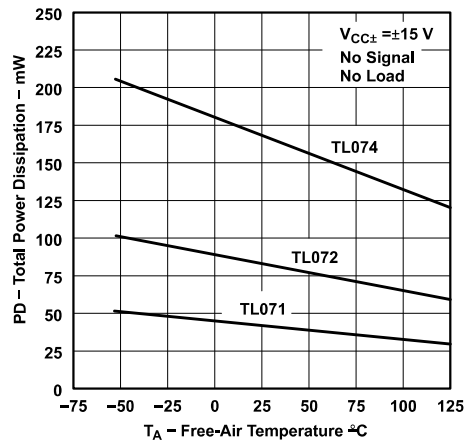


Figure 14. Total Power Dissipation vs Free-Air Temperature

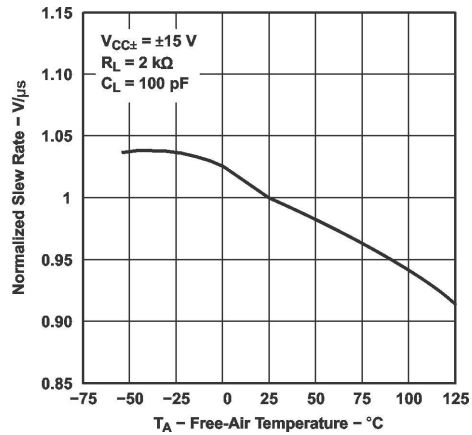


Figure 15. Normalized Slew Rate vs Free-Air Temperature

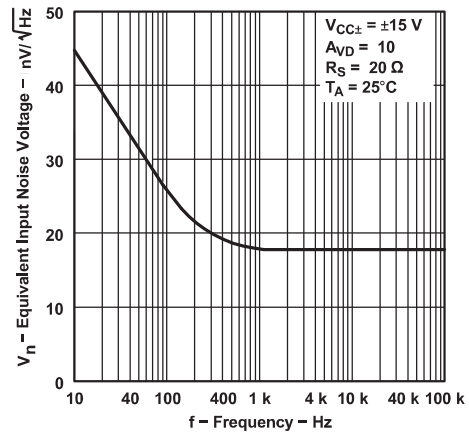


Figure 16. Equivalent Input Noise Voltage vs Frequency

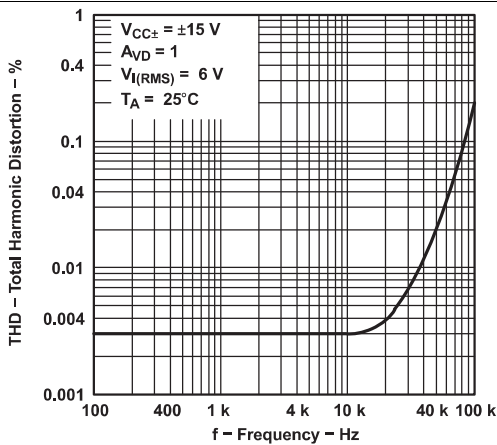


Figure 17. Total Harmonic Distortion vs Frequency

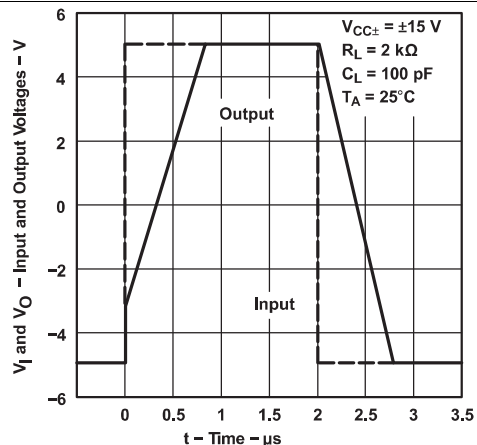
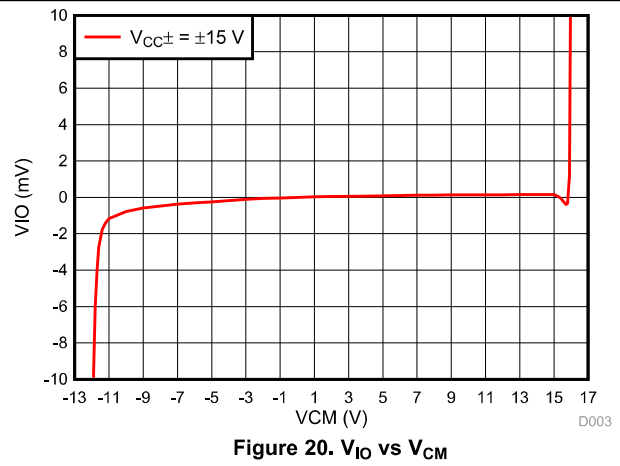
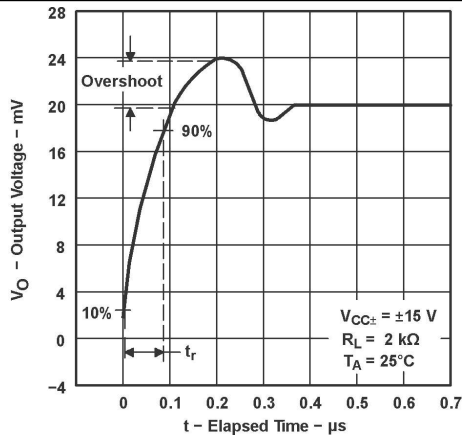


Figure 18. Voltage-Follower Large-Signal Pulse Response

Typical Characteristics (continued)



6.1 Parameter Measurement Information

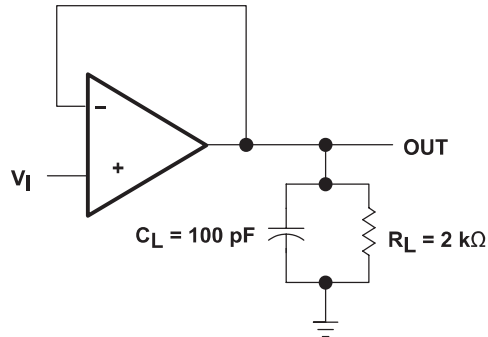


Figure 21. Unity-Gain Amplifier

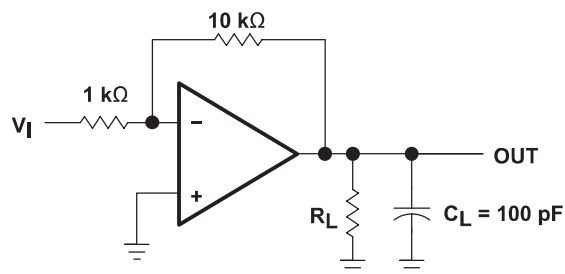


Figure 22. Gain-of-10 Inverting Amplifier

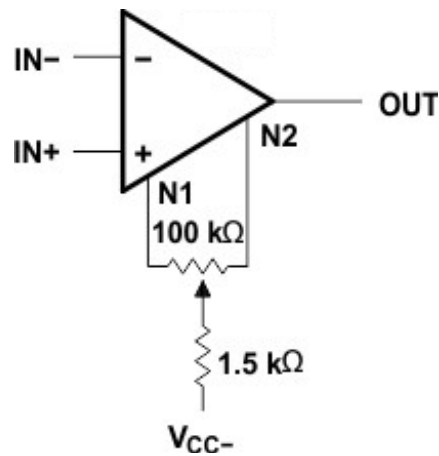


Figure 23. Input Offset-Voltage Null Circuit

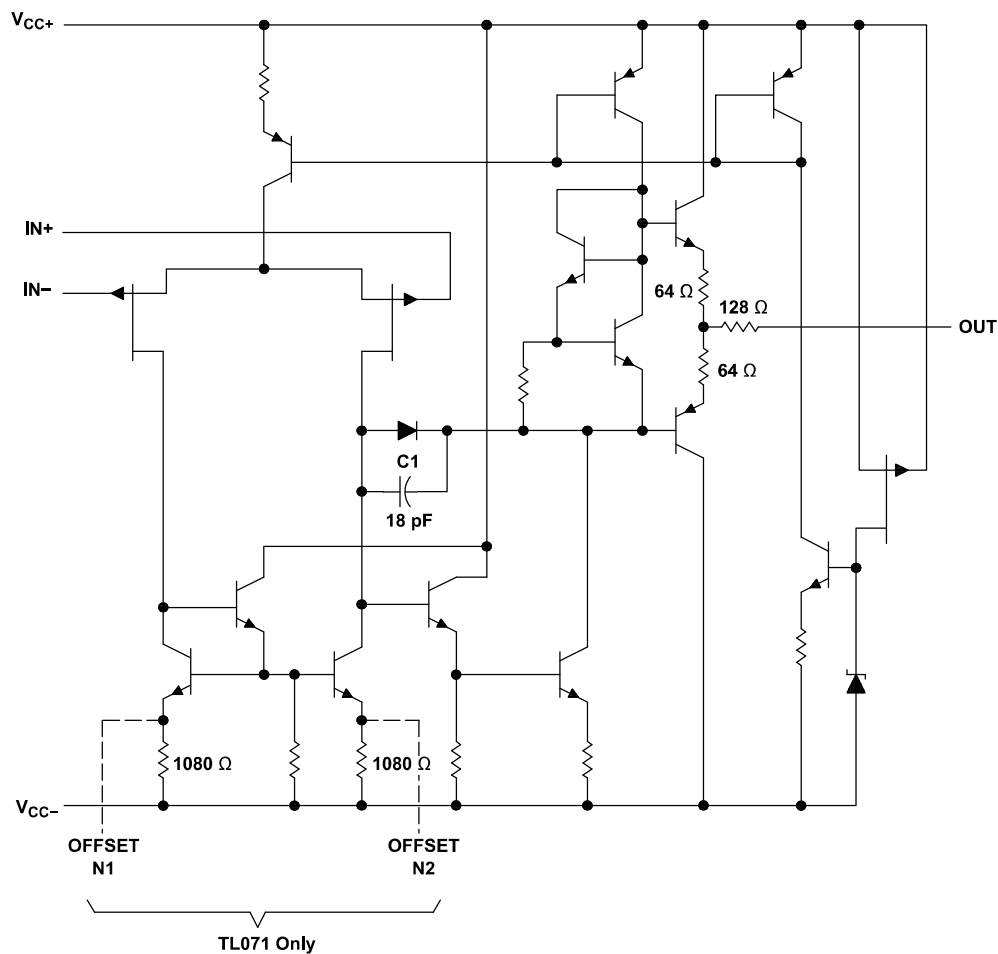
7 Detailed Description

7.1 Overview

The JFET-input operational amplifiers in the TL07xx series are similar to the TL08x series, with low input bias and offset currents, and a fast slew rate. The low harmonic distortion and low noise make the TL07xx series ideally suited for high-fidelity and audio preamplifier applications. Each amplifier features JFET inputs (for high input impedance) coupled with bipolar output stages integrated on a single monolithic chip.

The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to +85°C. The M-suffix devices are characterized for operation over the full military temperature range of -55°C to +125°C.

7.2 Functional Block Diagram



All component values shown are nominal.

COMPONENT COUNT†			
COMPONENT TYPE	TL071	TL072	TL074
Resistors	11	22	44
Transistors	14	28	56
JFET	2	4	6
Diodes	1	2	4
Capacitors	1	2	4
epi-FET	1	2	4

† Includes bias and trim circuitry

7.3 Feature Description

7.3.1 Total Harmonic Distortion

Harmonic distortions to an audio signal are created by electronic components in a circuit. Total harmonic distortion (THD) is a measure of harmonic distortions accumulated by a signal in an audio system. These devices have a very low THD of 0.003% meaning that the TL07x device adds little harmonic distortion when used in audio signal applications.

7.3.2 Slew Rate

The slew rate is the rate at which an operational amplifier can change the output when there is a change on the input. These devices have a 13-V/ μ s slew rate.

7.4 Device Functional Modes

These devices are powered on when the supply is connected. These devices can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.

8 Application and Implementation

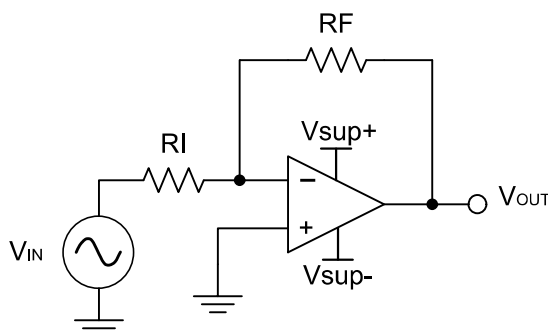
NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

A typical application for an operational amplifier is an inverting amplifier. This amplifier takes a positive voltage on the input, and makes the voltage a negative voltage. In the same manner, the amplifier makes negative voltages positive.

8.2 Typical Application



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Figure 24. Inverting Amplifier

8.2.1 Design Requirements

The supply voltage must be selected so the supply voltage is larger than the input voltage range and output range. For instance, this application scales a signal of ± 0.5 V to ± 1.8 V. Setting the supply at ± 12 V is sufficient to accommodate this application.

8.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier:

$$A_v = \frac{V_{OUT}}{V_{IN}} \quad (1)$$

$$A_v = \frac{1.8}{-0.5} = -3.6 \quad (2)$$

Once the desired gain is determined, select a value for R_I or R_F . Selecting a value in the kilohm range is desirable because the amplifier circuit uses currents in the milliamp range. This ensures the part does not draw too much current. This example uses $10 \text{ k}\Omega$ for R_I which means $36 \text{ k}\Omega$ is used for R_F . This is determined by [Equation 3](#).

$$A_v = -\frac{R_F}{R_I} \quad (3)$$

Typical Application (continued)

8.2.3 Application Curve

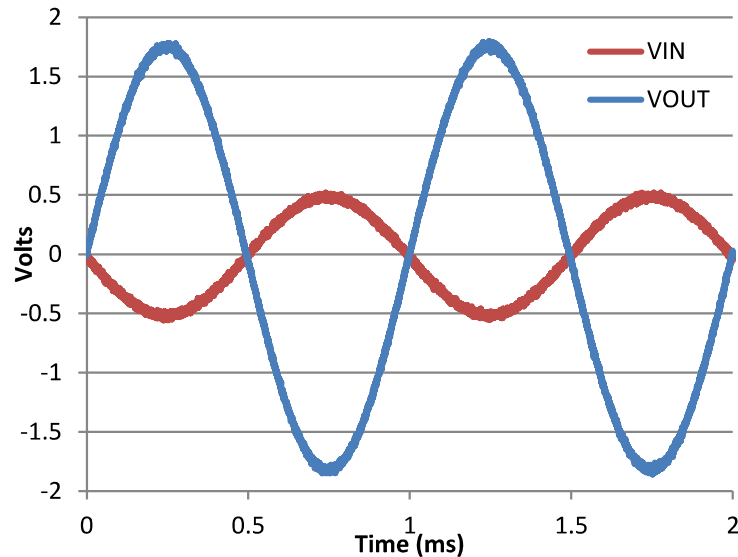
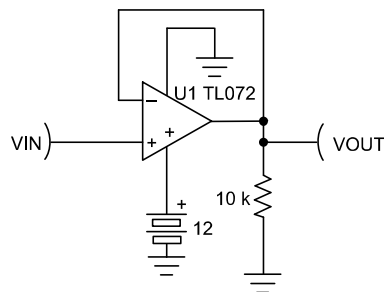


Figure 25. Input and Output Voltages of the Inverting Amplifier

8.3 Unity Gain Buffer



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Figure 26. Single-Supply Unity Gain Amplifier

8.3.1 Design Requirements

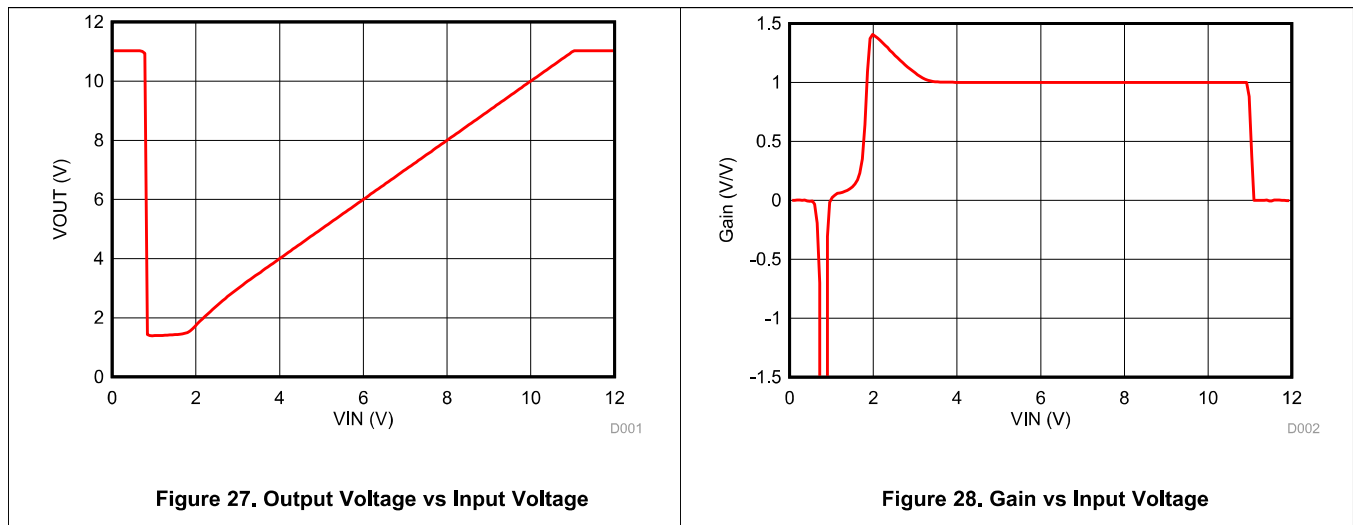
- V_{CC} must be within valid range per [Recommended Operating Conditions](#). This example uses a value of 12 V for V_{CC} .
- Input voltage must be within the recommended common-mode range, as shown in [Recommended Operating Conditions](#). The valid common-mode range is 4 V to 12 V ($V_{CC-} + 4$ V to V_{CC+}).
- Output is limited by output range, which is typically 1.5 V to 10.5 V, or $V_{CC-} + 1.5$ V to $V_{CC+} - 1.5$ V.

8.3.2 Detailed Design Procedure

- Avoid input voltage values below 1 V to prevent phase reversal where output goes high.
- Avoid input values below 4 V to prevent degraded V_{IO} that results in an apparent gain greater than 1. This may cause instability in some second-order filter designs.

Unity Gain Buffer (continued)

8.3.3 Application Curves



8.4 System Examples

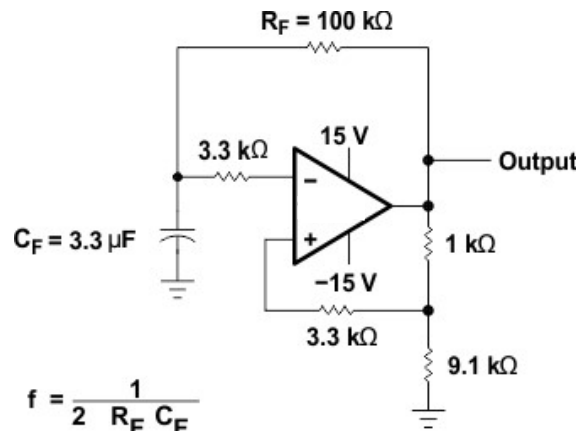


Figure 29. 0.5-Hz Square-Wave Oscillator

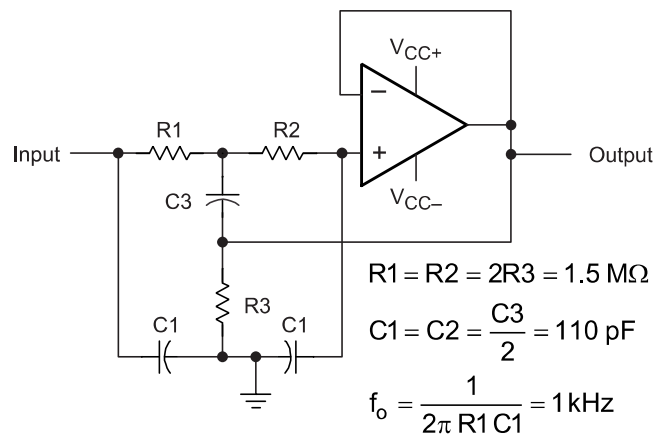


Figure 30. High-Q Notch Filter

System Examples (continued)

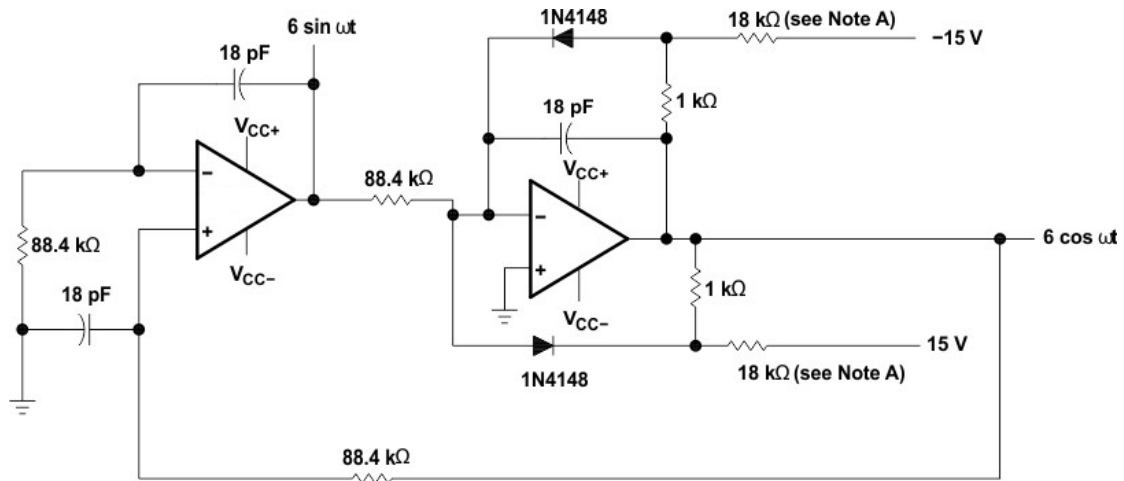


Figure 31. 100-kHz Quadrature Oscillator

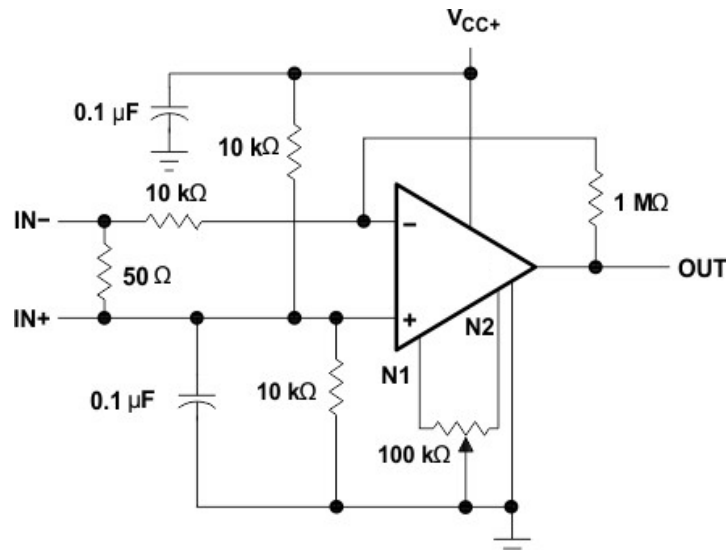


Figure 32. AC Amplifier

9 Power Supply Recommendations

CAUTION

Supply voltages larger than 36 V for a single-supply or outside the range of ± 18 V for a dual-supply can permanently damage the device (see the [Absolute Maximum Ratings](#)).

Place 0.1- μ F bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see [Layout](#).

10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see [Circuit Board Layout Techniques](#).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting input minimizes parasitic capacitance, as shown in [Layout Example](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

10.2 Layout Example

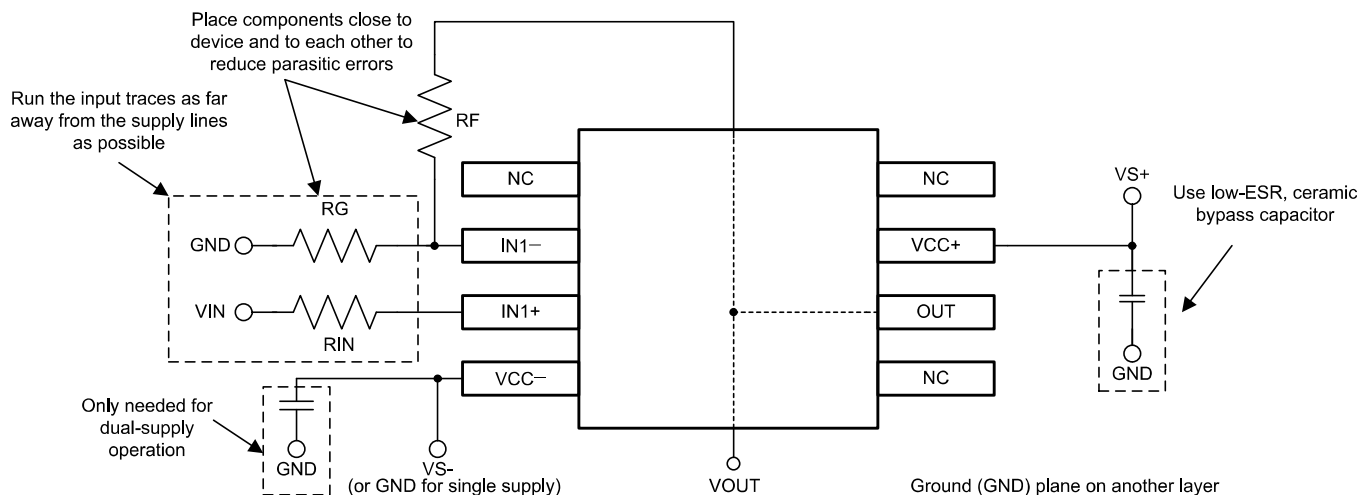


Figure 33. Operational Amplifier Board Layout for Noninverting Configuration

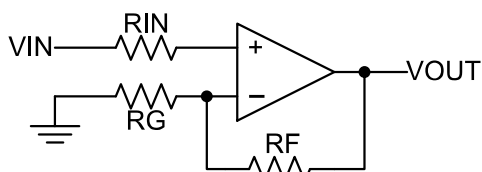


Figure 34. Operational Amplifier Schematic for Noninverting Configuration

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following:

[Circuit Board Layout Techniques](#) (SLOA089)

11.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 2. Related Links

PARTS	PRODUCT FOLDER	ORDER NOW	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TL071	Click here	Click here	Click here	Click here	Click here
TL071A	Click here	Click here	Click here	Click here	Click here
TL071B	Click here	Click here	Click here	Click here	Click here
TL072	Click here	Click here	Click here	Click here	Click here
TL072A	Click here	Click here	Click here	Click here	Click here
TL072B	Click here	Click here	Click here	Click here	Click here
TL072M	Click here	Click here	Click here	Click here	Click here
TL074	Click here	Click here	Click here	Click here	Click here
TL074A	Click here	Click here	Click here	Click here	Click here
TL074B	Click here	Click here	Click here	Click here	Click here
TL074M	Click here	Click here	Click here	Click here	Click here

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments.
 All other trademarks are the property of their respective owners.

11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.